

Most Frequently Occurring Classifications of Patents Returned  
From A Search of 10/660,779 on September 21, 2004

Combined Classifications

7 349/42  
6 257/315  
6 257/E27.103  
5 257/E27.111  
4 257/296  
4 257/59  
4 349/139  
4 349/54  
3 257/72  
3 257/E21.682  
3 257/E21.703  
3 257/E27.086  
3 349/149  
3 365/182  
3 445/24  
2 257/306  
2 257/314  
2 257/316  
2 257/506  
2 257/E21.414  
2 257/E21.648  
2 313/309  
2 313/336  
2 313/351  
2 313/497  
2 315/169.1  
2 345/92  
2 349/143  
2 349/152  
2 349/155  
2 349/187  
2 349/192  
2 365/149  
2 365/185.17  
2 365/185.19  
2 365/185.22  
2 365/185.24  
2 365/185.29  
2 365/185.32  
2 365/51  
2 438/158  
2 438/278  
2 438/296  
2 438/30  
2 438/48  
2 445/50

Titles of Most Frequently Occurring Classifications of Patents Returned  
From A Search of 10/660,779 on September 21, 2004

- 7 349/42 (2 OR, 5 XR)
  - Class 349 : LIQUID CRYSTAL CELLS, ELEMENTS AND SYSTEMS
  - 349/19 PARTICULAR EXCITATION OF LIQUID CRYSTAL
  - 349/33 .Electrical excitation of liquid crystal (i.e.,  
particular voltage pulses, AC vs. DC, threshold voltages,  
etc.)
  - 349/41 ..With particular switching device
  - 349/42 ...Transistor
  
- 6 257/315 (2 OR, 4 XR)
  - Class 257 : ACTIVE SOLID-STATE DEVICES
  - 257/264 ...Enhancement mode or with high resistivity  
channel (e.g., doping of  $10^{15}$  cm<sup>-3</sup> or less)
  - 257/288 .Having insulated electrode (e.g., MOSFET, MOS  
diode)
  - 257/314 ..Variable threshold (e.g., floating gate  
memory device)
  - 257/315 ...With floating gate electrode
  
- 4 257/296 (2 OR, 2 XR)
  - Class 257 : ACTIVE SOLID-STATE DEVICES
  - 257/264 ...Enhancement mode or with high resistivity  
channel (e.g., doping of  $10^{15}$  cm<sup>-3</sup> or less)
  - 257/288 .Having insulated electrode (e.g., MOSFET, MOS  
diode)
  - 257/296 ..Insulated gate capacitor or insulated gate  
transistor combined with capacitor (e.g., dynamic memory  
cell)
  
- 4 257/59 (2 OR, 2 XR)
  - Class 257 : ACTIVE SOLID-STATE DEVICES
  - 257/49 NON-SINGLE CRYSTAL, OR RECRYSTALLIZED,  
SEMICONDUCTOR MATERIAL FORMS PART OF ACTIVE JUNCTION  
(INCLUDING FIELD-INDUCED ACTIVE JUNCTION)
  - 257/52 .Amorphous semiconductor material
  - 257/57 ..Field effect device in amorphous  
semiconductor material
  - 257/59 ...In array having structure for use as imager  
or display, or with transparent electrode

PLUS Search Results for S/N 10/660,779, Searched September 21, 2004 (Top 50)

The Patent Linguistics Utility System (PLUS) is a USPTO automated search system for U.S. Patents from 1971 to the present. PLUS is a query-by-example search system which produces a list of patents that are most closely related linguistically to the application searched. This search was prepared by the staff of the Scientific and Technical Information Center, SIRA.

6524876	5581382	5959319	5307189	6028653
5852305	5628661	6056783	5365474	6071776
6031247	5691793	6060350	5472898	6107670
5841490	5939833	6351065	5529943	6181605
5654727	6042444	5227996	5637895	6232620
5661050	6127714	5643817	5684547	6304489
5735721	6137219	6247743	5747843	6344999
5026143	6630976	4247918	5790222	6353557
5489933	5763919	4984199	5859677	6462373
5504601	4881066	5255219	5962889	5223735